The products are transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diodeas the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

High isolation 3750 VRMS
Operating temperature range -55°C to 125°C
RoHS & REACH Compliance
HBM: H3A; MM: M4; CDM:C3
CQC approved
VDE approved
UL approved

(Temperature=25°C)

Parameter		**Symbol**	**Value**	**Unit**
Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750	Vrms
Operating Temperature		T_{opr}	-55~+125	
Junction Temperature		T_j	135	
Storage Temperature		T_{stg}	-55~+125	

Soldering Temperature	T_{sol}	260	

: μ

:

(Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	I_F=10mA	-	1.2	1.5	V
	Reverse Current	I_R	V_R=6V	-	-	1	μA
	Terminal Capacitance	C_t	V=0, f=1MHz	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	V_{CE}=20V, I_F=0	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	I_C=0.1mA I_F=0	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	I_E=0.1mA I_F=0	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	I_F=5mA V_{CE}=5V	100	-	400	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_F=20mA I_C=1mA	-	0.06	0.2	V
	Isolation resistance	R_{IO}	DC500V 40~60%R.H.	10^{12}	10^{14}	-	Ω
	Floating Capacitance	C_{IO}	V=0, f=1MHz	-	0.4	1	pF
	Cut-off Frequency	f_c	V_{CE}=5V, I_C=2mA R_L=100Ω, -3dB	-	80	-	kHz
	Rise Time	t_r	V_{CE}=2V, I_C=2mA R_L=100Ω	-	3	18	μs
	Fall Time	t_f		-	4	18	μs
	Response Time	t_{on}		-	6	25	μs
		t_{off}		-	5	25	μs

:

CTR Rank	Min. (%)	Max. (%)	Test Condition
P	200	400	I_F=0.5mA, V_{CE}=5V
	200	400	I_F=5mA, V_{CE}=5V
Q	100	300	I_F=0.5mA, V_{CE}=5V
	100	300	I_F=5mA, V_{CE}=5V

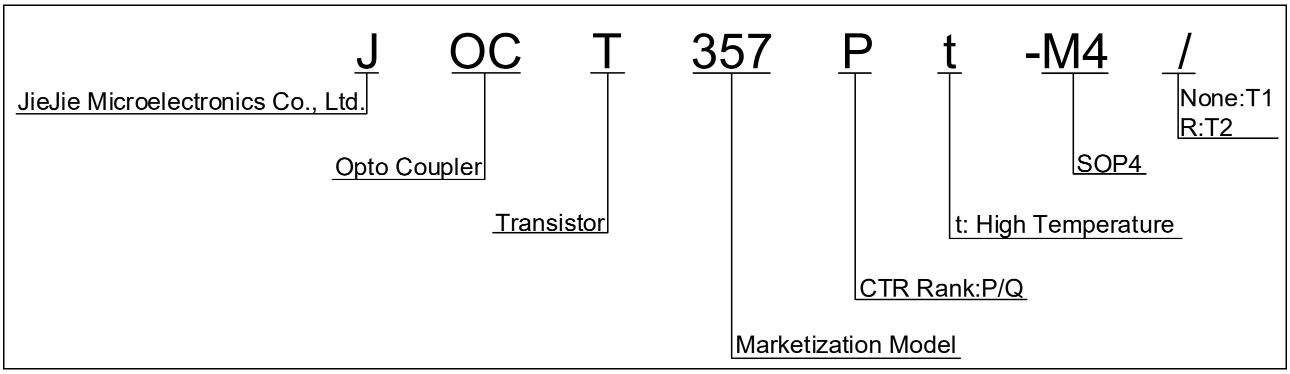

J
OC
T
357
P
t
-M4
/
JieJie Microelectronics Co., Ltd.
Opto Coupler
Transistor
Marketization Model
CTR Rank:P/Q
t: High Temperature
SOP4
None:T1
R:T2

FIG.1: Max. Allowable LED Forward Current vs. Ambient Temperature

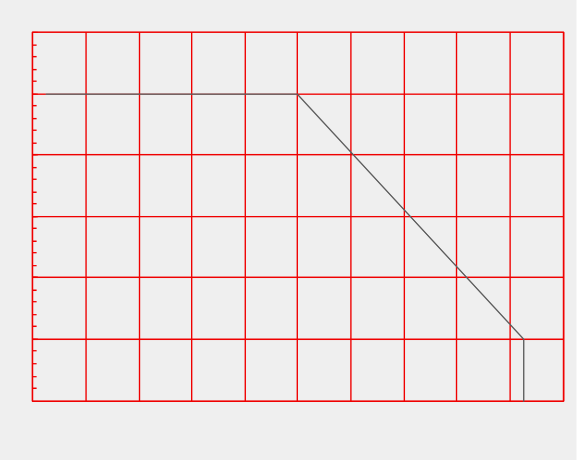


FIG.2: Collector Power Dissiption vs. Ambient Temperature

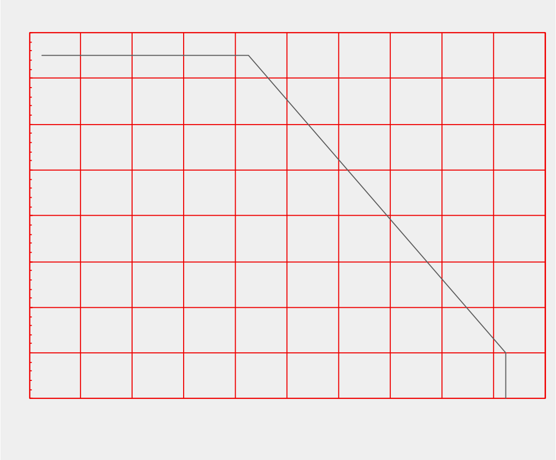


FIG.3: Forward Current vs. Forward Voltage

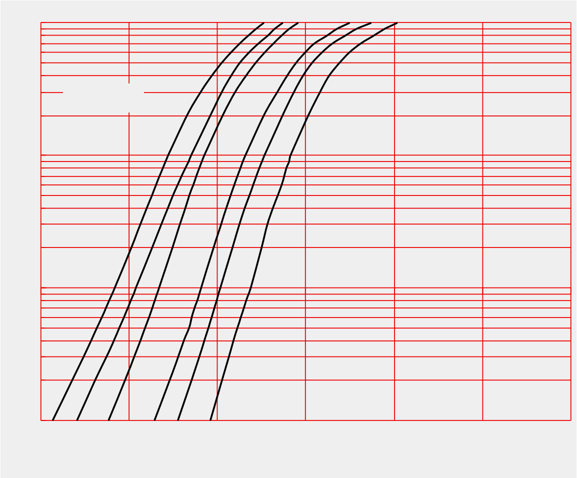


FIG.4: Normalized Collector Dark Current vs. Ambient Temperature

FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

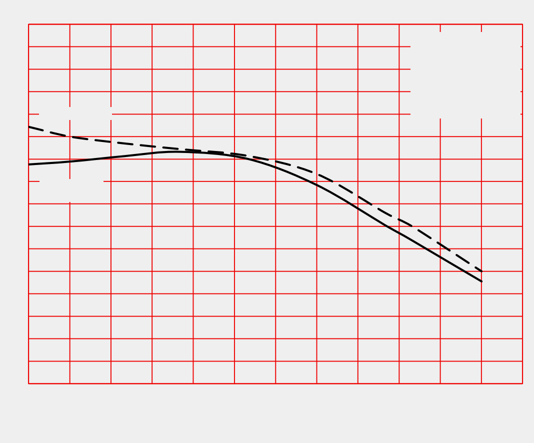


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

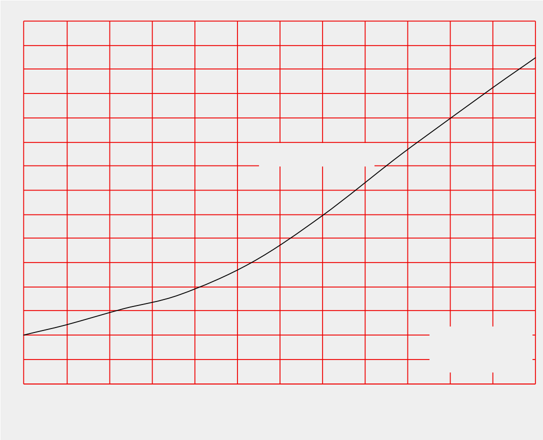


FIG.9: Response Time vs. Load Resistance

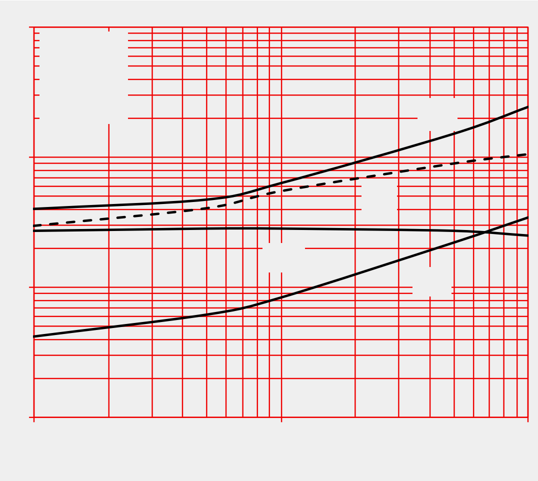


FIG.10: Frequency Response

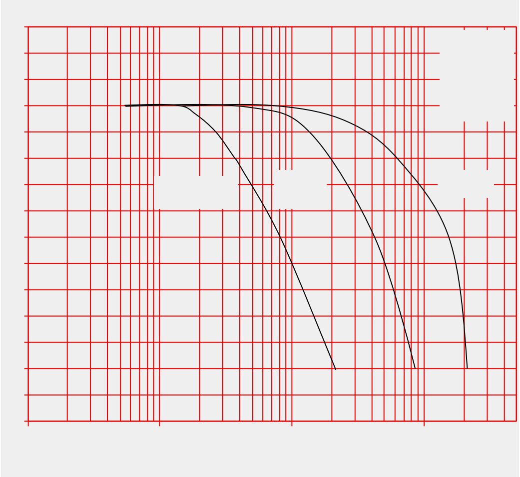


FIG.11: Test Circuits of Response Time

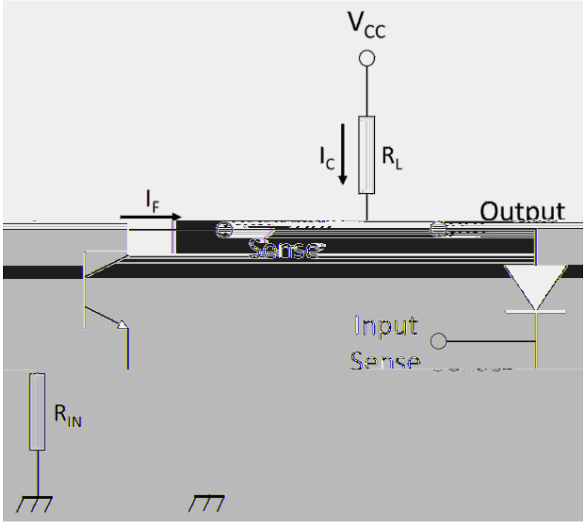


FIG.12: Curves of Response Time

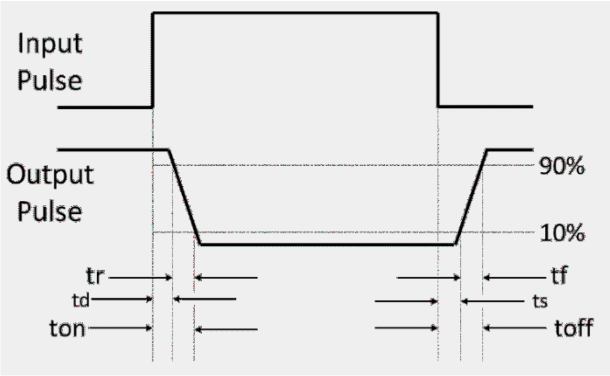
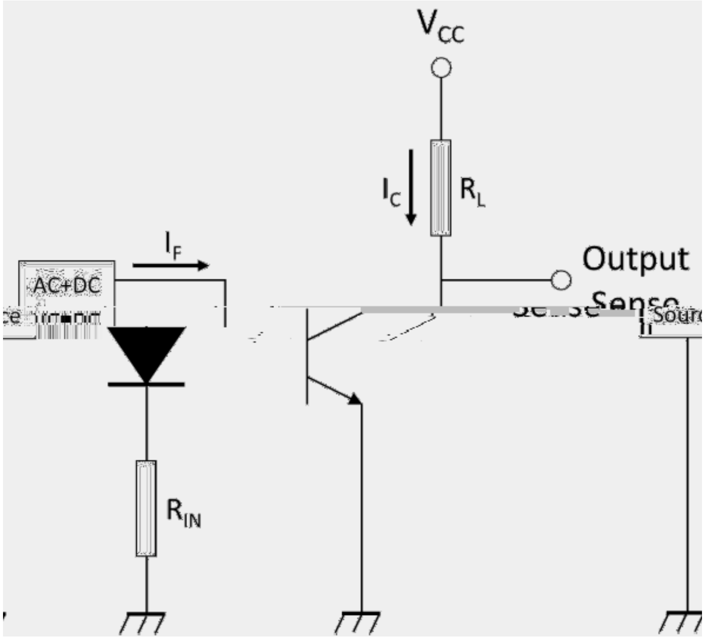
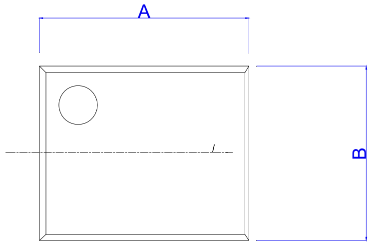
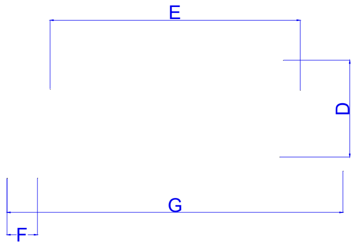
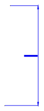


FIG.13: Test Circuits of Frequency Response



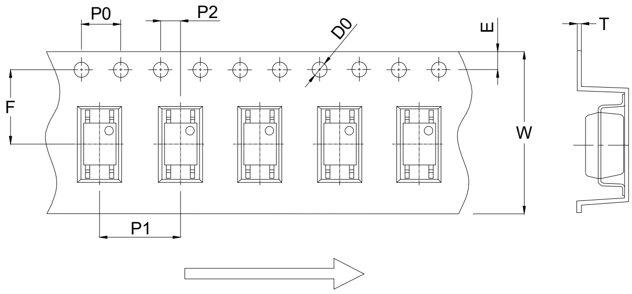






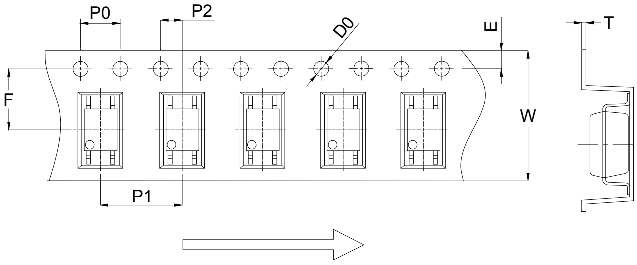
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C						
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F						
G	6.70			0.264		
H						
I						
J						

Option None

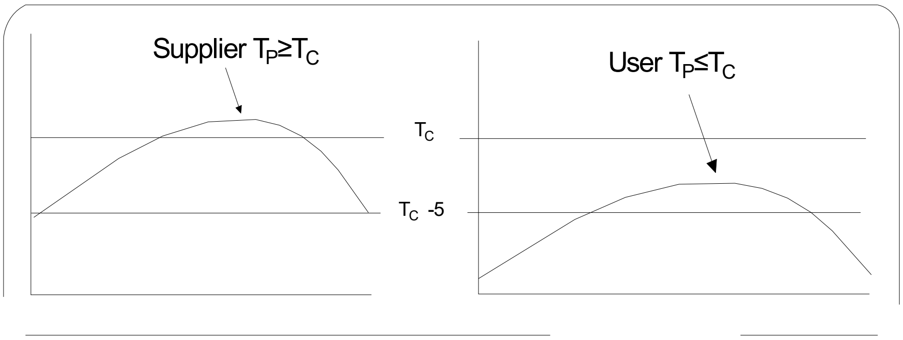


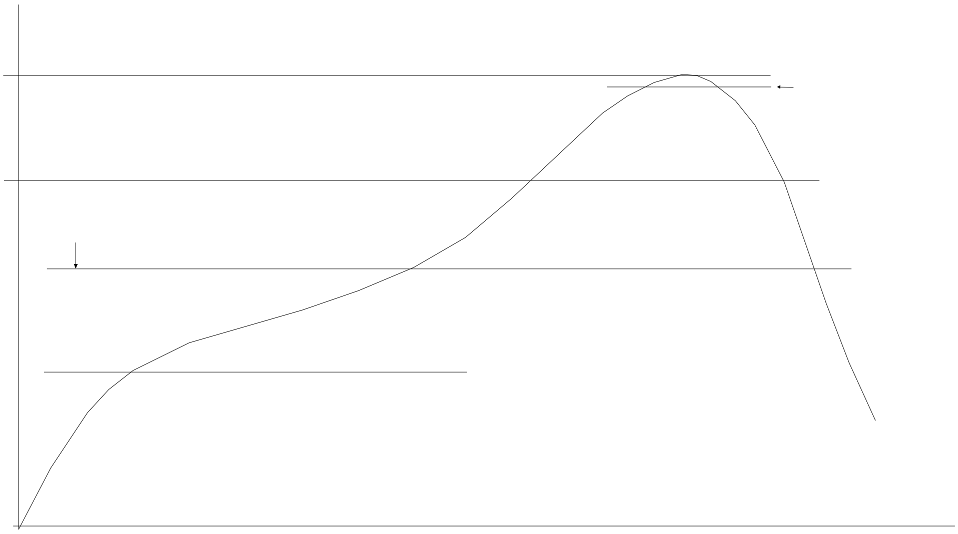
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.27	0.30	0.33	0.011	0.012	0.013
W	15.80	16.00	16.20	0.622	0.630	0.638

Option R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484


Supplier T_P≥T_C
User T_P≤T_C
T_C
T_C -5



Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.

2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.

3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.

4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.

5. The component has a shelf life of o m d m s t b μ